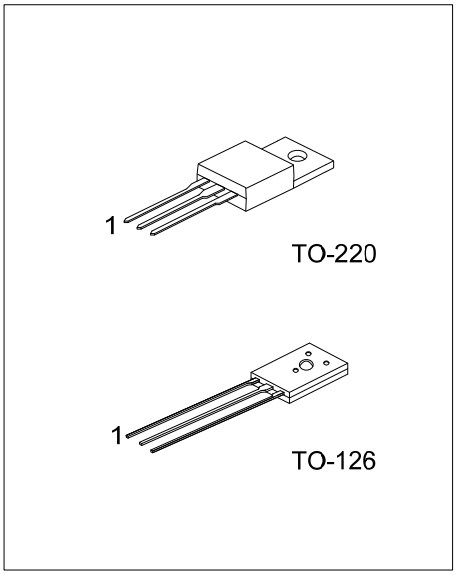
TIP127

PNP SILICON TRANSISTOR

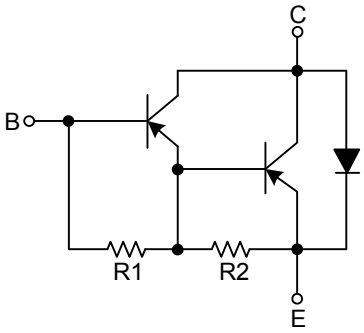
PNP EPITAXIAL TRANSISTOR



■ DESCRIPTION

The UTC **TIP127** is a PNP epitaxial transistor, designed for use in general purpose amplifier low-speed switching applications.

■ EQUIVALENT TEST (R_1 ≈8kΩ, R_2 ≈0.12kΩ)



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
TIP127L-T60-K	TIP127G-T60-K	TO-126	E	C	B	Bulk
TIP127L-TA3-T	TIP127G-TA3-T	TO-220	B	C	E	Tube

TIP127L-T60-K (1)Packing Type (2)Package Type (3)Lead Plating	(1) K: Bulk, T: Tube (2) T60: TO-126, TA3: TO-220 (3) G: Halogen Free, L: Lead Free

■ ABSOLUTE MAXIMUM RATING (T_a = 25°C, unless otherwise specified)

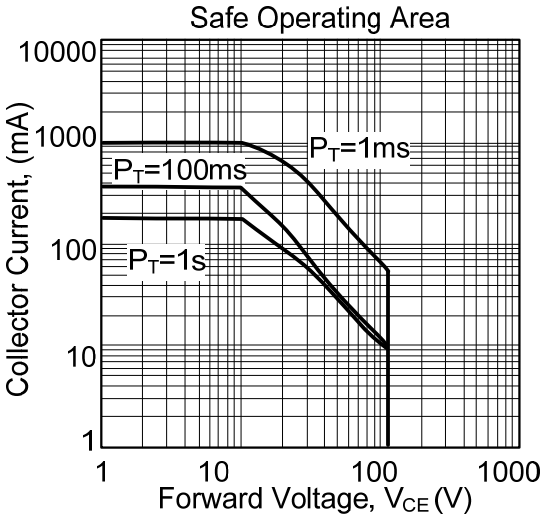
PARAMETER		SYMBOL	RATINGS	UNIT
Collector to Base Voltage		V_{CBO}	100	V
Collector to Emitter Voltage		V_{CEO}	100	V
Emitter to Base Voltage		V_{EBO}	5	V
Collector Current		I_C	5	A
Power Dissipation	TO-126	P_D	40	W
	TO-220		65	W
Junction Temperature		T_J	150	°C
Operating Temperature		T_{OPR}	-20 ~ +85	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

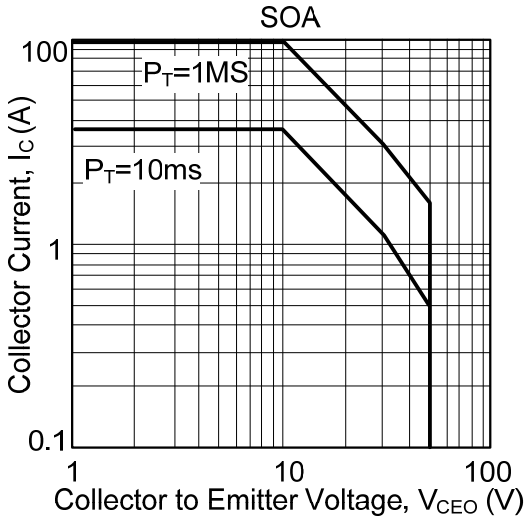
Note: Absolute maximum ratings are the values beyond which the device will be damaged permanently.
Absolute maximum ratings are only stress ratings and it is not implied for functional device operation.

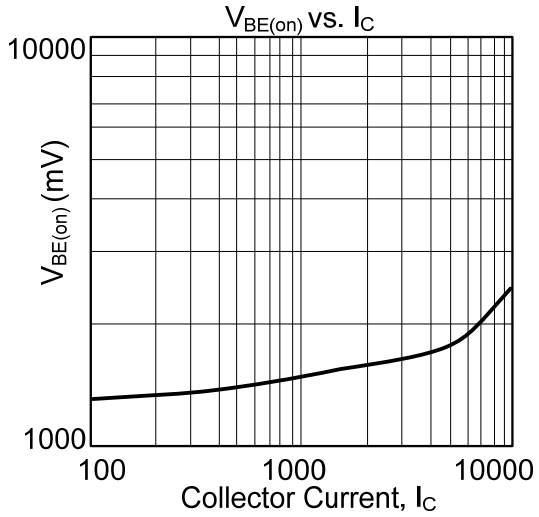
■ ELECTRICAL CHARACTERISTICS (T_a =25°C, unless otherwise specified)

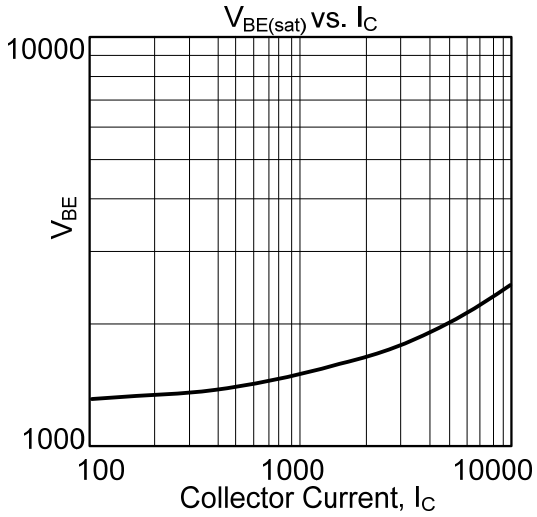
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=100mA	100			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=100V			200	uA
Collector-Cut-Off Current	I_{CEO}	V_{CE}=50V			500	uA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=5V			2	mA
Collector-Emitter Saturation Voltage	$V_{CE(SAT)1}$	I_C=3A, I_B=12mA			2	V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)2}$	I_C=5A, I_B=20mA			4	V
Base-Emitter Saturation Voltage	$V_{BE(ON)}$	V_{CE}=3V, I_C=3A			2.5	V
DC Current Gain	h_{FE}	I_C=500mA, V_{CE}=3V I_C=3A, V_{CE}=3V	1			K

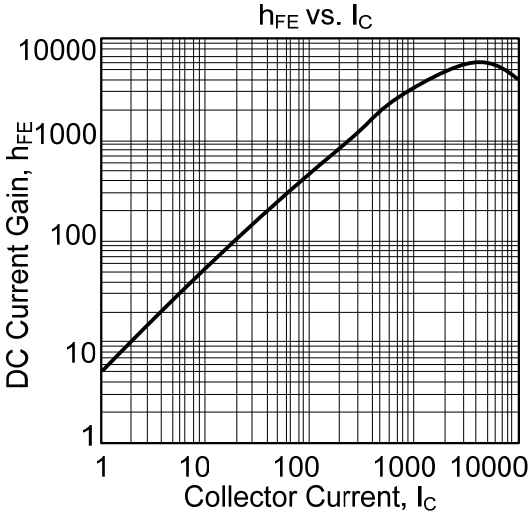
■ TYPICAL CHARACTERISTICS

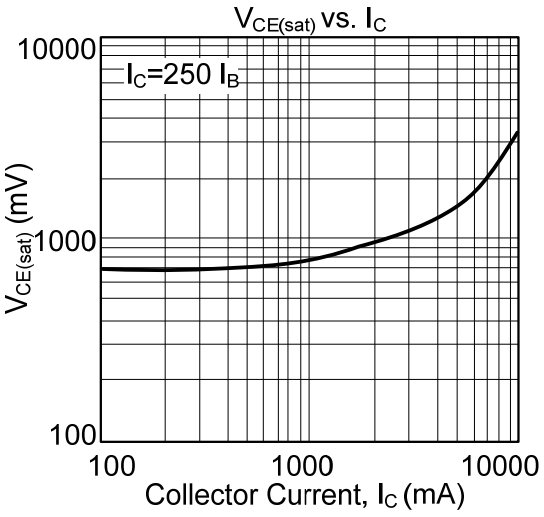












■ TYPICAL CHARACTERISTICS(Cont.)